	Type	L #	Hits	Search Text	DBs
1	BRS	L1	62	violette near michael.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	1768	438/257.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	78	2 and (select near line$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	5	2 and ((select near line$1) near25 (nand))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	436	((select near line$1) near25 (nand))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	23	((select near line$1) near25 (nand near string))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	2	((select near line$1) near25 (nand)) near25 (dielectric or insulat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	3	((select near line$1 or sl) near25 (nand)) near25 (dielectric or insulat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	42	((select) near25 (nand)) near25 (dielectric or insulat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	35	((conduct$3 or poly$4) near25 (nand)) near25 (dielectric or insulat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
11	BRS	L11	28306	(third) near3 (conductiv$3 or polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12	BRS	L12	37	(third) near3 (conductiv$3 or polysilicon) near15 (nand)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	75	(second) near3 (conductiv$3 or polysilicon) near15 (nand)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L14	1921	(contact or hole$1) near25 (nand)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L15	67	((contact or hole$1) near25 (nand)) near15 (polysilicon or conductiv$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L16	83	((opening or via or aperture) near25 (nand)) near15 (polysilicon or conductiv$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	1	((recess$3) near25 (nand)) near15 (polysilicon or conductiv$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	U	1	Document ID	Title
1			US 20040026748 A1	Semiconductor device with source line and fabrication method thereof
2	X		US 20040014286 A1	Method of forming a select line in a NAND type flash memory device
3	X		US 6777294 B2	Method of forming a select line in a NAND type flash memory device